

7MBR75XPE120-50

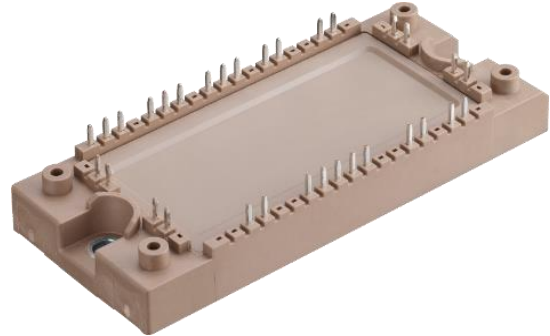
IGBT Modules

Power Module(X series)
1200V / 75A / PIM

■ **Features**

- Low $V_{CE(sat)}$
- Compact Package
- P.C.Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit
- RoHS compliant Product

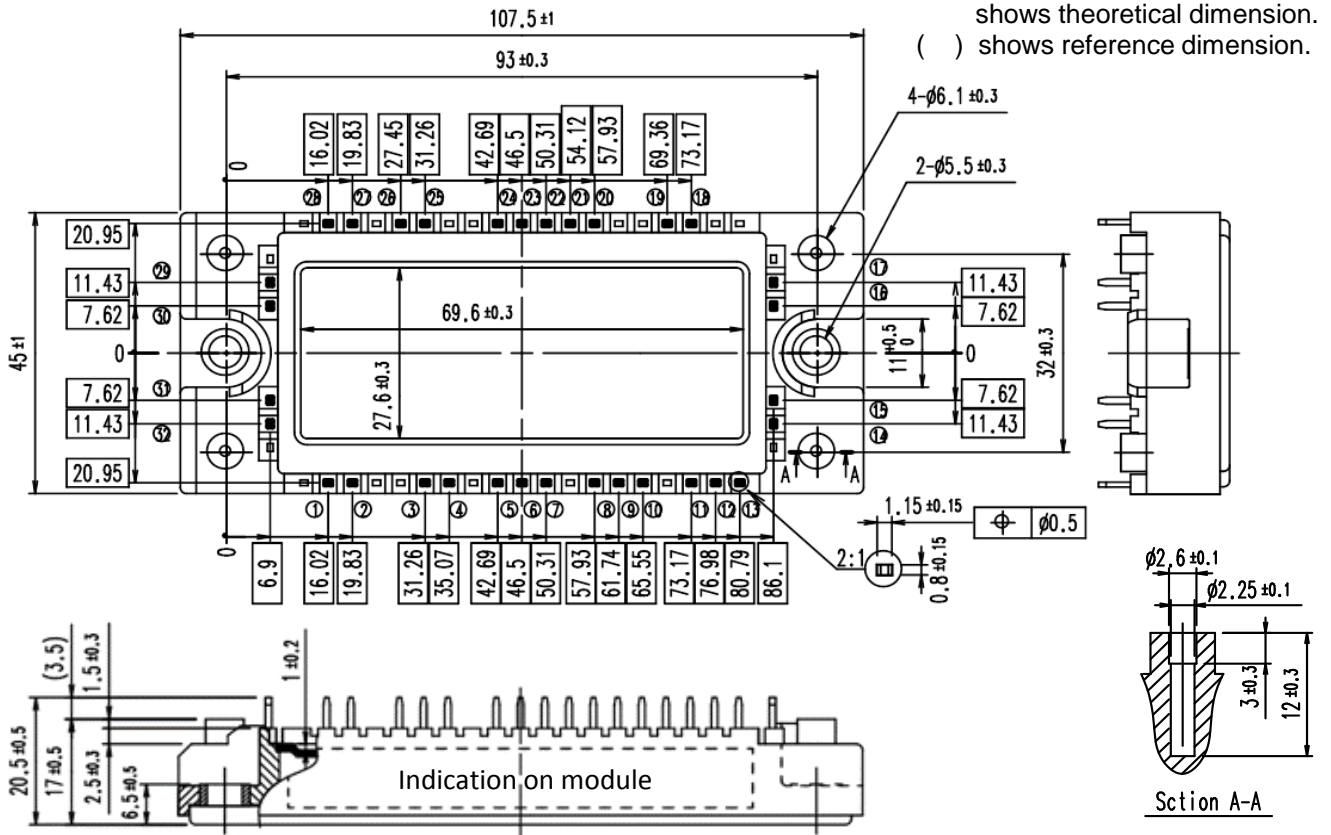
■ **Typical appearance**



■ **Applications**

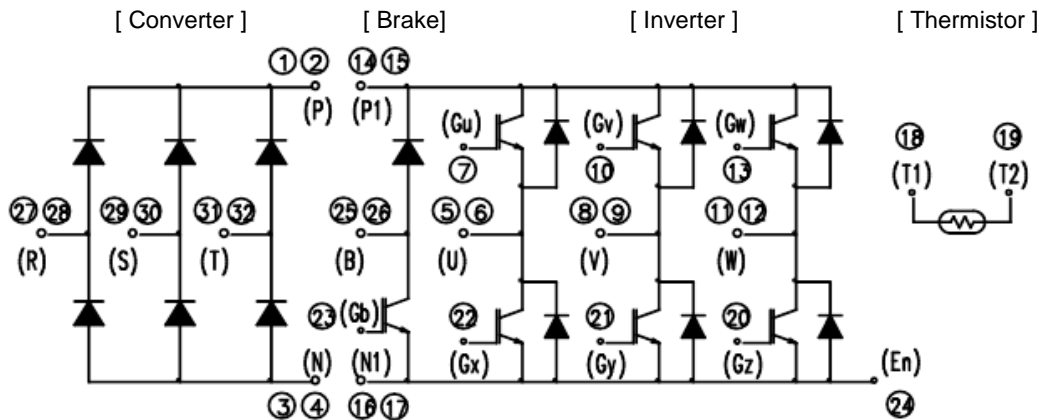
- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply

■ **Outline drawing (Unit : mm)**



Weight: 200 g (typ.)

■ **Equivalent circuit**



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IGBT Modules
■ Maximum ratings (at $T_c = 25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions	Maximum ratings	Units	
Inverter	Collector-Emitter voltage	V_{CES}		1200	V	
	Gate-Emitter voltage	V_{GES}		± 20	V	
	Collector current	I_C	Continuous	$T_c=100^\circ\text{C}$	75	A
		I_C pulse	1ms		150	
	Forward current	I_F	Continuous		75	
		I_F pulse	1ms		150	
Collector power dissipation	P_C	1 device		455	W	
Brake IGBT	Collector-Emitter voltage	V_{CES}		1200	V	
	Gate-Emitter voltage	V_{GES}		± 20	V	
	Collector current	I_C	Continuous	$T_c=100^\circ\text{C}$	35	A
		I_C pulse	1ms		70	
Collector power dissipation	P_C	1 device		200	W	
Brake FWD	Forward current	I_F	Continuous	15	A	
		I_{FRM}	1ms	30		
Converter	Repetitive peak reverse voltage	V_{RRM}		1200	V	
	Repetitive peak reverse voltage	V_{RRM}		1600	V	
	Average output current	I_O	Three-phase full wave rectified current	$T_c=80^\circ\text{C}$	75	A
	Surge current (Non-Repetitive) (*1)	I_{FSM}	$t=10\text{ms}$, Half sine wave form	$T_{vj}=25^\circ\text{C}$	630	A
				$T_{vj}=150^\circ\text{C}$	520	
I^2t (Non-Repetitive) (*1)	I^2t		$T_{vj}=25^\circ\text{C}$	2000	A^2s	
			$T_{vj}=150^\circ\text{C}$	1350		
Junction temperature	T_{vj}	Inverter, Brake		175	$^\circ\text{C}$	
		Converter		150		
Operating junction temperature (under switching conditions)	T_{vjop}	Inverter, Brake		175		
		Converter		150		
Case temperature	T_c			125		
Storage temperature	T_{stg}			-40 ~ 125		
Isolation voltage	between terminals and copper base (*2)	V_{iso}	A.C. : 1min.	2500	Vrms	
	between thermistor and others (*3)					
Screw torque (*4)	Mounting	-	M5	6.0	N·m	

(*1) T_{vj} : Temperature at test start.

(*2) All terminals should be connected together during the test.

(*3) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

(*4) Recommendable value : Mounting 2.5 ~ 6.0 N·m (M5)

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IGBT Modules
■ Electrical characteristics (at $T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero Gate voltage collector current	I_{CES}	$V_{GE} = 0\text{V}$ $V_{CE} = 1200\text{V}$	-	-	50	μA	
Gate-Emitter leakage current	I_{GES}	$V_{CE} = 0\text{V}$ $V_{GE} = +20/-20\text{V}$	-	-	100	nA	
Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20\text{V}$ $I_C = 75\text{mA}$	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15\text{V}$ $I_C = 75\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	1.75	2.25	V
			$T_{vj}=25^{\circ}\text{C}$	-	1.55	2.00	
	$T_{vj}=125^{\circ}\text{C}$		-	1.95	-		
	$T_{vj}=150^{\circ}\text{C}$		-	2.05	-		
	$T_{vj}=175^{\circ}\text{C}$		-	2.10	-		
$V_{CE(sat)}$ (chip)							
Internal Gate resistance	r_g	-	-	0	-	Ω	
Capacitance	C_{ies}	$V_{CE} = 10\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$	-	TBD	-	nF	
	C_{oes}		-	TBD	-		
	C_{res}		-	TBD	-		
Gate charge	Q_G	$V_{CC} = 600\text{V}$ $V_{GE} = -15 \rightarrow +15\text{V}$ $I_C = 75\text{A}$	-	470	-	nC	
Forward voltage	V_F (terminal)	$I_F = 75\text{A}$	$T_{vj}=25^{\circ}\text{C}$	-	2.25	2.75	V
	V_F (chip)		$T_{vj}=25^{\circ}\text{C}$	-	2.05	2.50	
			$T_{vj}=125^{\circ}\text{C}$	-	2.15	-	
			$T_{vj}=150^{\circ}\text{C}$	-	2.15	-	
			$T_{vj}=175^{\circ}\text{C}$	-	2.10	-	
Switching time (*1)	$t_{d(on)}$	$V_{CC} = 600\text{V}$ $I_C, I_F = 75\text{A}$ $L_s = 30\text{nH}$ $V_{GE} = +15/-15\text{V}$ $R_G = 12\ \Omega$	$T_{vj}=25^{\circ}\text{C}$	-	TBD	-	μs
			$T_{vj}=125^{\circ}\text{C}$	-	TBD	-	
			$T_{vj}=150^{\circ}\text{C}$	-	TBD	-	
			$T_{vj}=175^{\circ}\text{C}$	-	TBD	-	
	t_r		$T_{vj}=25^{\circ}\text{C}$	-	TBD	-	
			$T_{vj}=125^{\circ}\text{C}$	-	TBD	-	
			$T_{vj}=150^{\circ}\text{C}$	-	TBD	-	
			$T_{vj}=175^{\circ}\text{C}$	-	TBD	-	
	$t_{d(off)}$		$T_{vj}=25^{\circ}\text{C}$	-	TBD	-	
			$T_{vj}=125^{\circ}\text{C}$	-	TBD	-	
			$T_{vj}=150^{\circ}\text{C}$	-	TBD	-	
			$T_{vj}=175^{\circ}\text{C}$	-	TBD	-	
t_f	$T_{vj}=25^{\circ}\text{C}$	-	TBD	-			
	$T_{vj}=125^{\circ}\text{C}$	-	TBD	-			
	$T_{vj}=150^{\circ}\text{C}$	-	TBD	-			
	$T_{vj}=175^{\circ}\text{C}$	-	TBD	-			
Reverse recovery time	t_{rr}	$T_{vj}=25^{\circ}\text{C}$	-	TBD	-		
		$T_{vj}=125^{\circ}\text{C}$	-	TBD	-		
		$T_{vj}=150^{\circ}\text{C}$	-	TBD	-		
		$T_{vj}=175^{\circ}\text{C}$	-	TBD	-		

(*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$

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IGBT Modules

Items	Symbols	Conditions	Characteristics			Units				
			min.	typ.	max.					
Inverter Switching loss (per pulse)	E_{on}	$V_{CC} = 600V$ $I_C, I_F = 75A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 12 \Omega$	$T_{vj}=25^\circ C$	-	4.65	-	mJ			
			$T_{vj}=125^\circ C$	-	5.92	-				
			$T_{vj}=150^\circ C$	-	6.51	-				
			$T_{vj}=175^\circ C$	-	7.08	-				
	E_{off}	$V_{CC} = 600V$ $I_C, I_F = 75A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 12 \Omega$	$T_{vj}=25^\circ C$	-	5.31	-				
			$T_{vj}=125^\circ C$	-	6.92	-				
			$T_{vj}=150^\circ C$	-	7.41	-				
			$T_{vj}=175^\circ C$	-	7.89	-				
	E_{rr}	$V_{CC} = 600V$ $I_C, I_F = 75A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 12 \Omega$	$T_{vj}=25^\circ C$	-	2.02	-				
			$T_{vj}=125^\circ C$	-	3.62	-				
			$T_{vj}=150^\circ C$	-	4.22	-				
			$T_{vj}=175^\circ C$	-	4.77	-				
Zero Gate voltage collector current	I_{CES}	$V_{GE} = 0V$ $V_{CE} = 1200V$		-	-	50	μA			
Gate-Emitter leakage current	I_{GES}	$V_{CE} = 0V, \quad V_{GE} = +20/-20V$		-	-	100	nA			
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15V$ $I_C = 35A$	$T_{vj}=25^\circ C$	-	1.60	2.05	V			
			$T_{vj}=25^\circ C$	-	1.50	1.95				
	$T_{vj}=125^\circ C$		-	1.85	-					
	$T_{vj}=150^\circ C$		-	1.95	-					
Collector-Emitter saturation voltage	$V_{CE(sat)}$ (chip)	$T_{vj}=150^\circ C$	-	1.95	-					
		$T_{vj}=175^\circ C$	-	2.00	-					
		Internal Gate resistance			r_g	-	0	-	Ω	
		Brake Switching time (*1)	$t_{d(on)}$	$V_{CC} = 600V$ $I_C = 35A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 30 \Omega$	$T_{vj}=25^\circ C$	-	0.10	-	μs	
$T_{vj}=125^\circ C$	-				0.10	-				
$T_{vj}=150^\circ C$	-				0.11	-				
$T_{vj}=175^\circ C$	-				0.11	-				
t_r	$V_{CC} = 600V$ $I_C = 35A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 30 \Omega$		$T_{vj}=25^\circ C$	-	0.04	-				
			$T_{vj}=125^\circ C$	-	0.05	-				
			$T_{vj}=150^\circ C$	-	0.05	-				
			$T_{vj}=175^\circ C$	-	0.05	-				
$t_{d(off)}$	$V_{CC} = 600V$ $I_C = 35A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 30 \Omega$		$T_{vj}=25^\circ C$	-	0.23	-				
			$T_{vj}=125^\circ C$	-	0.27	-				
			$T_{vj}=150^\circ C$	-	0.27	-				
			$T_{vj}=175^\circ C$	-	0.27	-				
t_f	$V_{CC} = 600V$ $I_C = 35A \quad L_s = 30nH$ $V_{GE} = +15/-15V$ $R_G = 30 \Omega$		$T_{vj}=25^\circ C$	-	0.12	-				
			$T_{vj}=125^\circ C$	-	0.18	-				
			$T_{vj}=150^\circ C$	-	0.20	-				
			$T_{vj}=175^\circ C$	-	0.21	-				
Reverse current	I_{RRM}	$V_R = 1200V$		-	-	50	μA			
Forward voltage	V_F (terminal)	$I_F = 15A$	$T_{vj}=25^\circ C$	-	1.90	2.35	V			
			$T_{vj}=25^\circ C$	-	1.80	2.25				
	V_F (chip)		$T_{vj}=125^\circ C$	-	1.85	-				
			$T_{vj}=150^\circ C$	-	1.80	-				
Reverse current	I_{RRM}	$V_R = 1600V$	$T_{vj}=175^\circ C$	-	1.75	-				
			Converter							
			Reverse current	I_{RRM}	$V_R = 1600V$		-	-	50	μA
			Forward voltage	V_{FM}	$I_F = 75A$	terminal	-	1.35	1.85	V
chip	-	1.15				1.60				
Thermistor	Resistance	$T = 25^\circ C$		-	5000	-	Ω			
		$T = 100^\circ C$		465	495	520				
B value	B	$T = 25/50^\circ C$		3305	3375	3450	K			

 (*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$
FM6M01719a

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NOTICE:

The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

■ Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.33	°C/W
		Inverter FWD	-	-	0.55	
		Brake IGBT	-	-	0.74	
		Brake FWD	-	-	1.85	
		Converter Diode	-	-	0.72	
Contact thermal resistance (1 IGBT+1 FWD) (*1)	$R_{th(c-f)}$	with 1 W/(m·K) thermal grease	-	0.05	-	

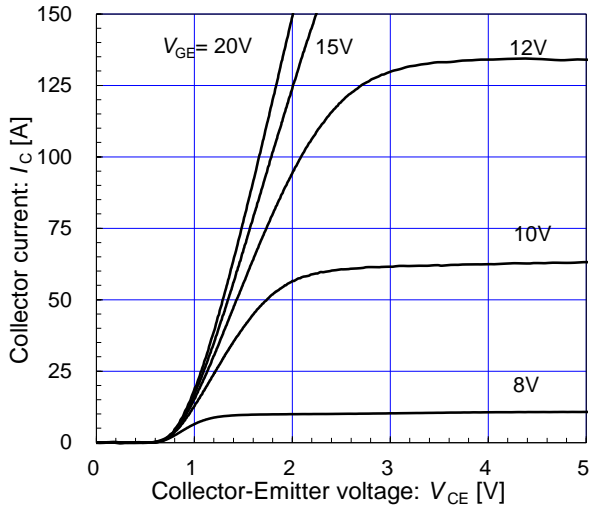
(*1) This is the value which is defined mounting on the additional cooling fin with thermal grease.

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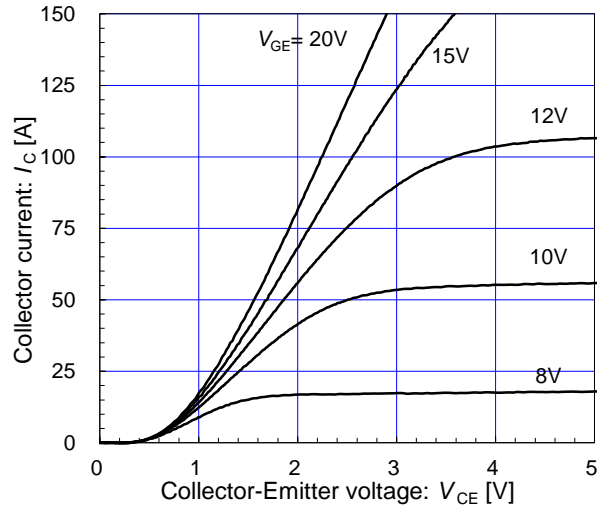
[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)
 $T_{vj} = 25^\circ\text{C} / \text{chip}$



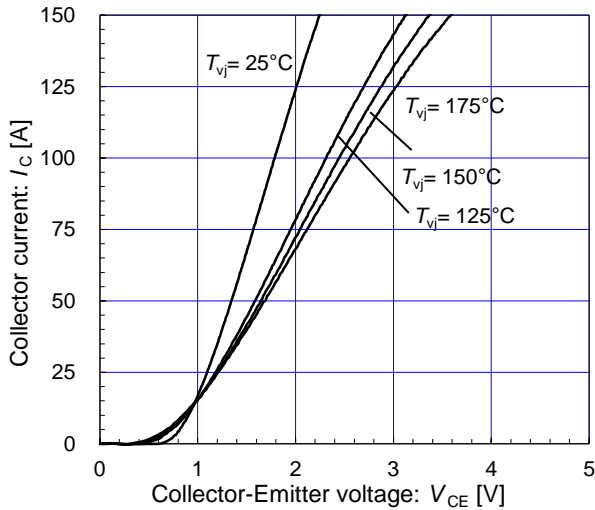
[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)
 $T_{vj} = 175^\circ\text{C} / \text{chip}$



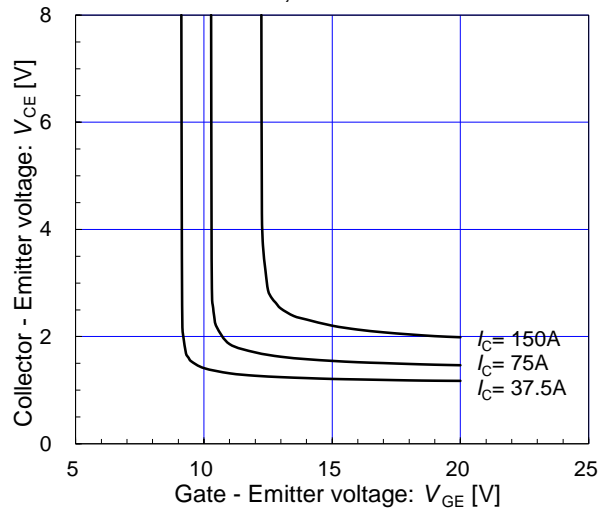
[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)
 $V_{GE} = 15\text{V} / \text{chip}$



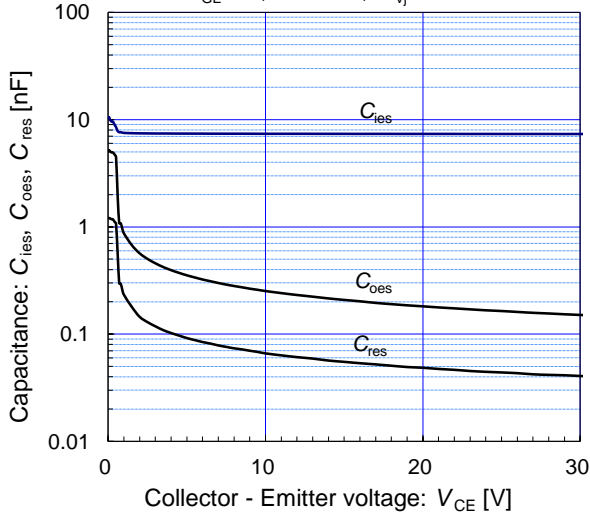
[Inverter]

Collector-Emittor voltage vs. Gate-Emittor voltage (typ.)
 $T_{vj} = 25^\circ\text{C} / \text{chip}$



[Inverter]

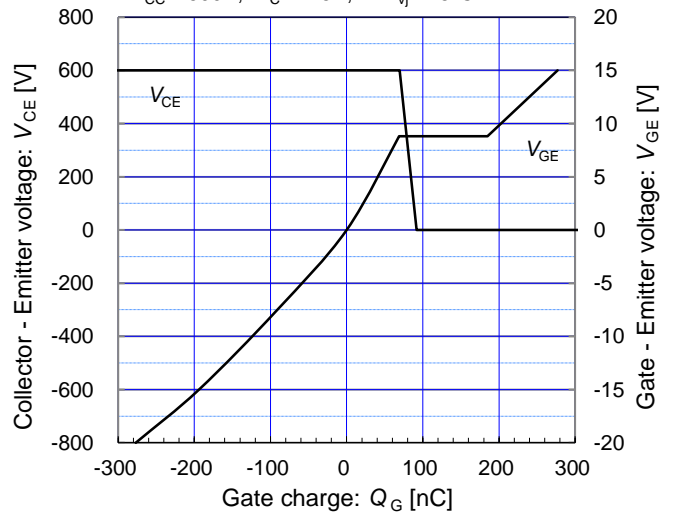
Capacitance vs. Collector-Emittor voltage (typ.)
 $V_{GE} = 0\text{V}, f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}$



[Inverter]

Dynamic Gate charge (typ.)

$V_{CC} = 600\text{V}, I_c = 75\text{A}, T_{vj} = 25^\circ\text{C}$

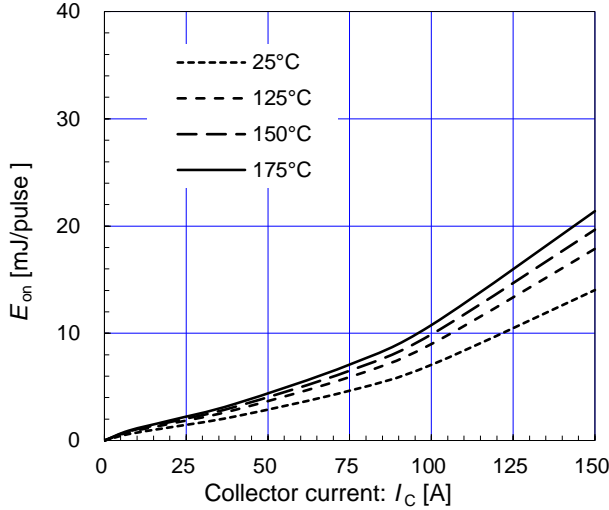


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[Inverter]

E_{on} vs. Collector current (typ.)

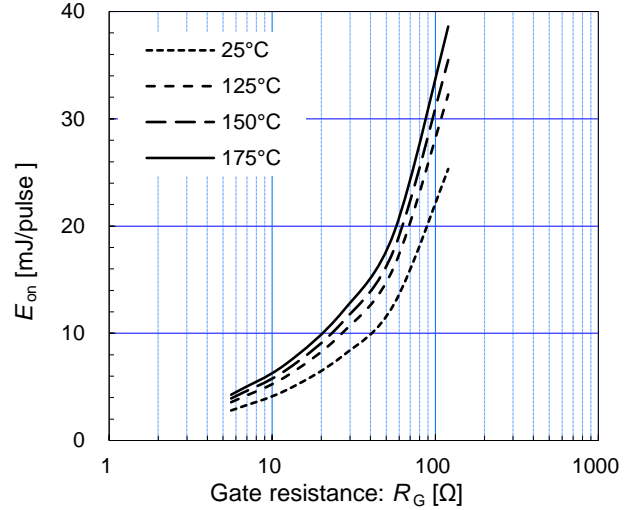
$V_{CC}=600V, V_{GE}=+15/-15V, R_G=12\Omega$



[Inverter]

E_{on} vs. Gate resistance (typ.)

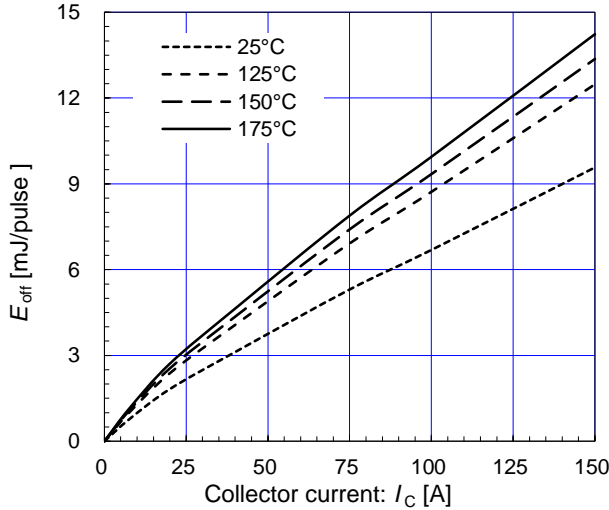
$V_{CC}=600V, V_{GE}=+15/-15V, I_C=75A$



[Inverter]

E_{off} vs. Collector current (typ.)

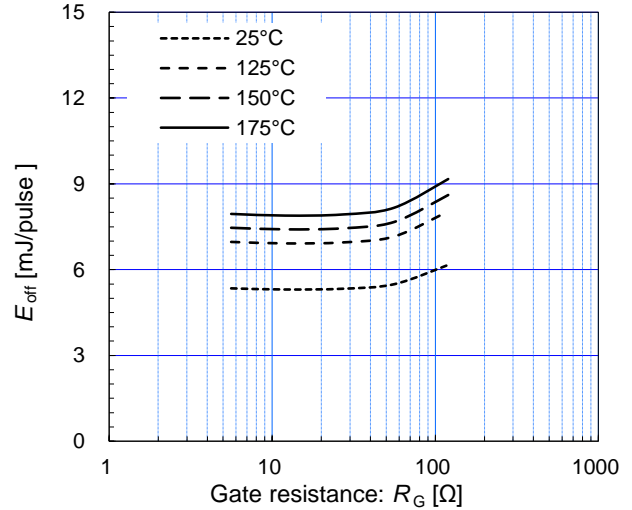
$V_{CC}=600V, V_{GE}=+15/-15V, R_G=12\Omega$



[Inverter]

E_{off} vs. Gate resistance (typ.)

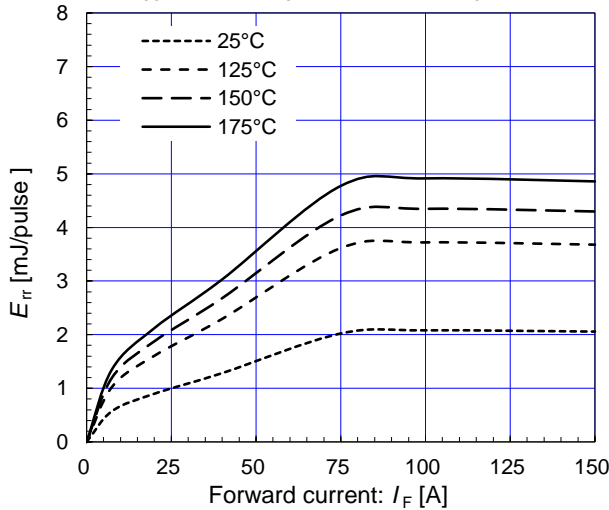
$V_{CC}=600V, V_{GE}=+15/-15V, I_C=75A$



[Inverter]

E_{rr} vs. Forward current (typ.)

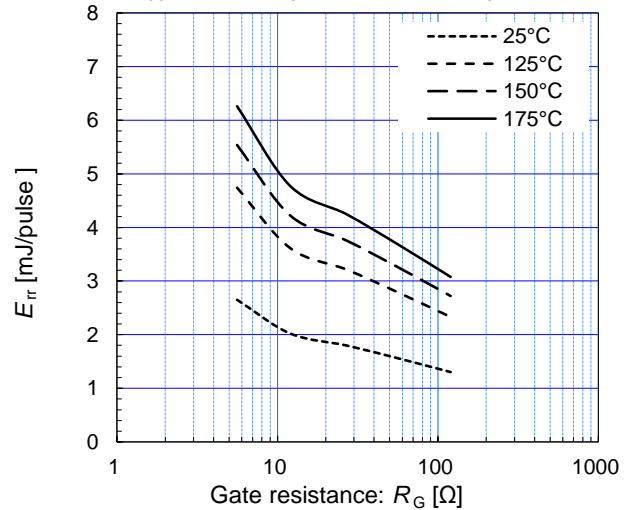
$V_{CC}=600V, V_{GE}=+15/-15V, R_G=12\Omega$



[Inverter]

E_{rr} vs. Gate resistance (typ.)

$V_{CC}=600V, V_{GE}=+15/-15V, I_C=75A$



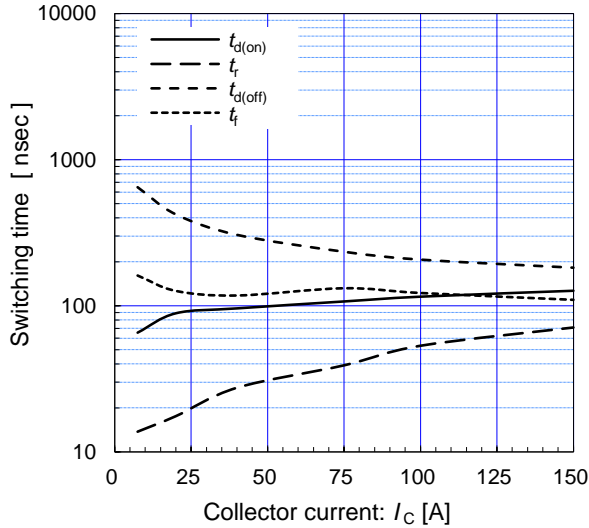
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[Inverter]

Switching time vs. Collector current (typ.)

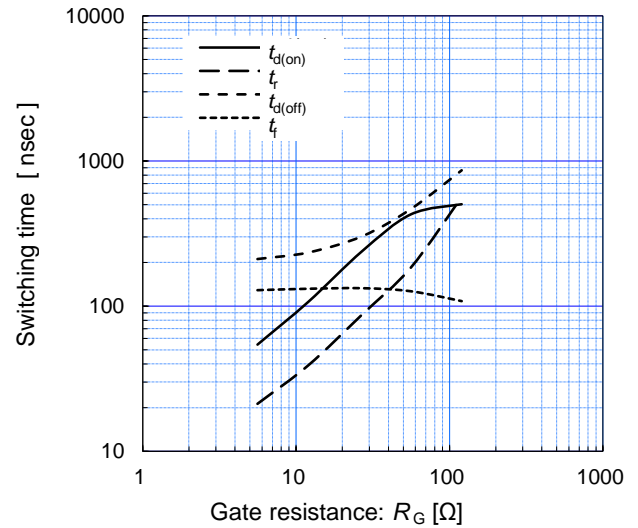
$V_{CC}=600V, R_G=12\Omega, V_{GE}=+15/-15V, T_{vj}=25^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

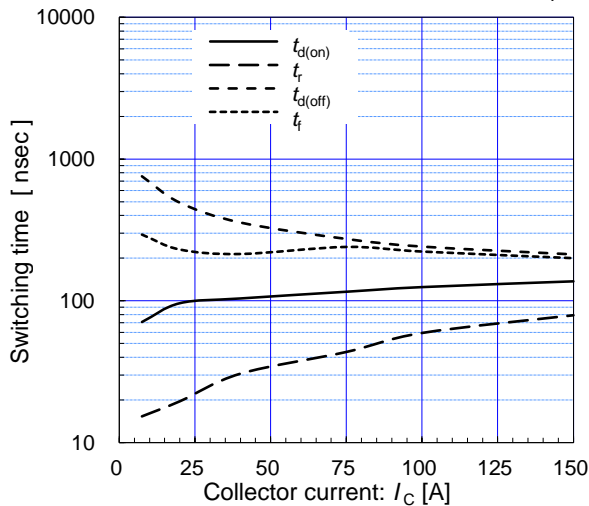
$V_{CC}=600V, I_C=75A, V_{GE}=+15/-15V, T_{vj}=25^\circ C$



[Inverter]

Switching time vs. Collector current (typ.)

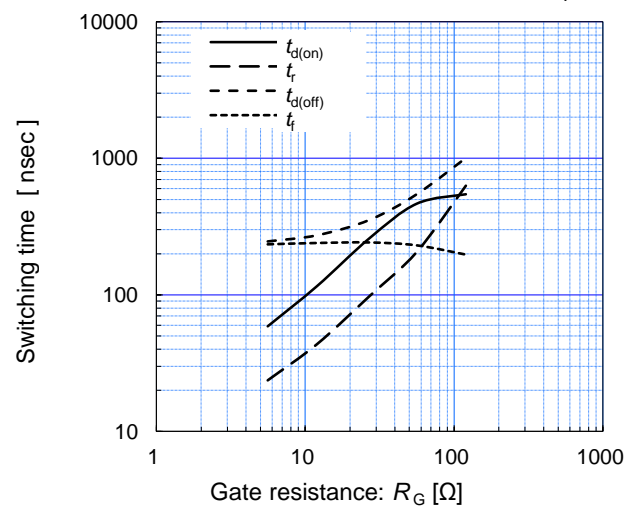
$V_{CC}=600V, R_G=12\Omega, V_{GE}=+15/-15V, T_{vj}=175^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

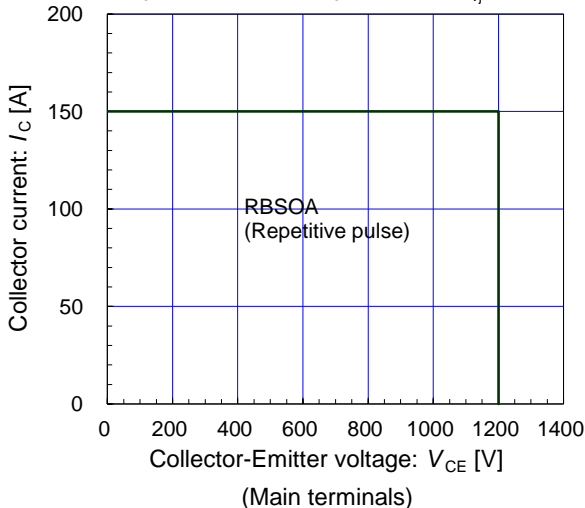
$V_{CC}=600V, I_C=75A, V_{GE}=+15/-15V, T_{vj}=175^\circ C$



[Inverter]

Reverse bias safe operating area (max.)

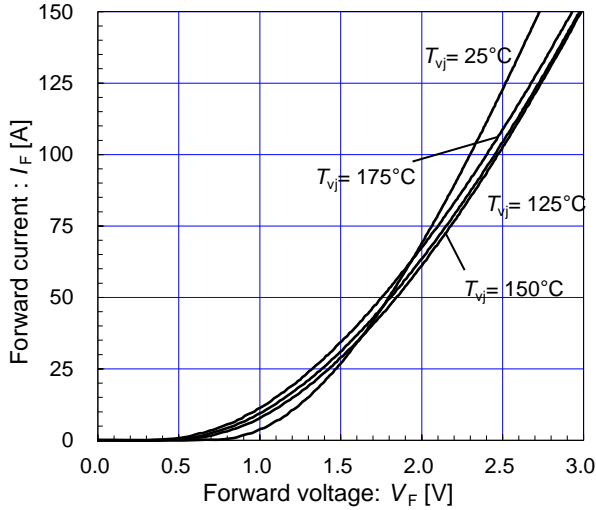
$V_{GE}=+15/-15V, R_G \geq 12\Omega, T_{vj}=175^\circ C$



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[Inverter]

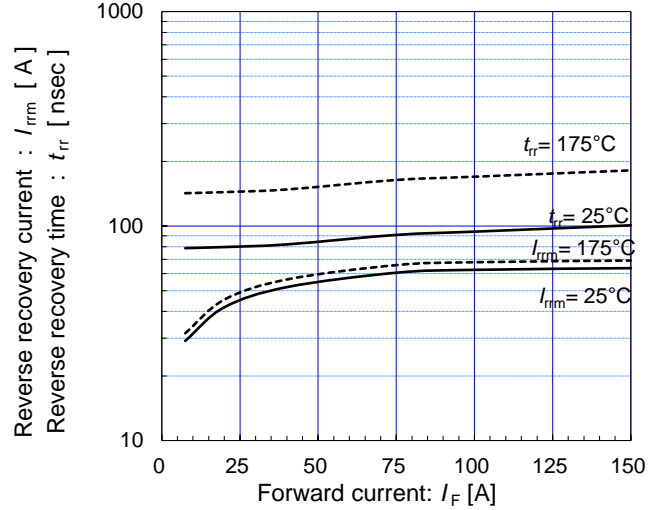
Forward current vs. Forward voltage (typ.)
chip



[Inverter]

Reverse recovery characteristics (typ.)

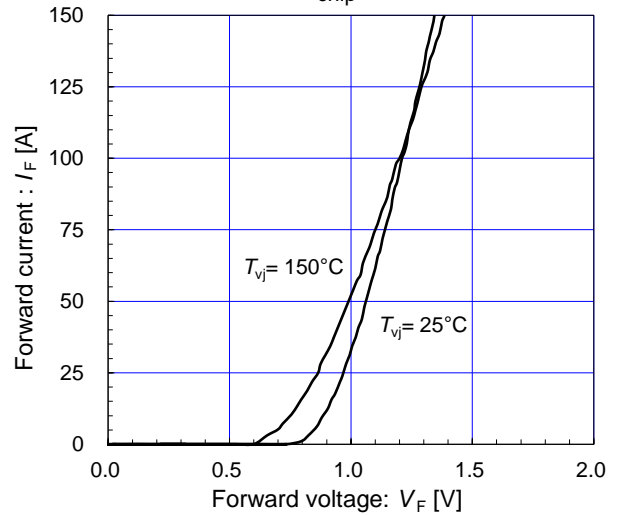
$V_{CC} = 600V, V_{GE} = +15/-15V, R_G = 12\Omega$



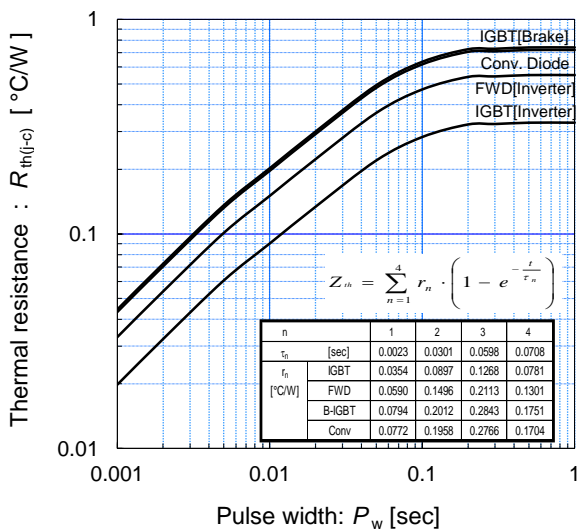
[Converter]

Forward current vs. Forward voltage (typ.)

chip

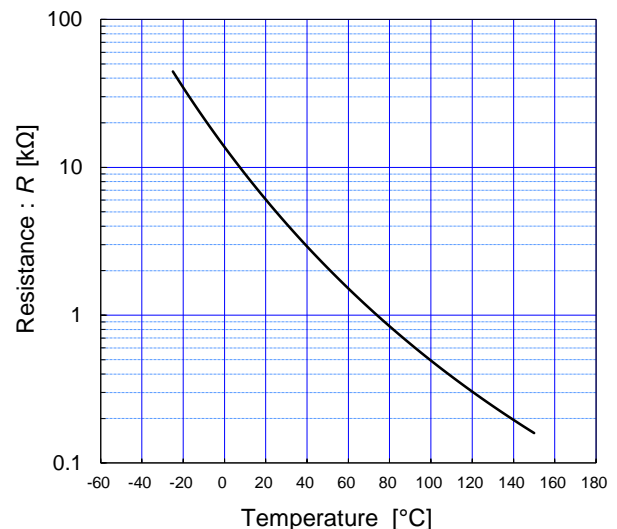


Transient thermal resistance (max.)



[Thermistor]

Temperature characteristic (typ.)

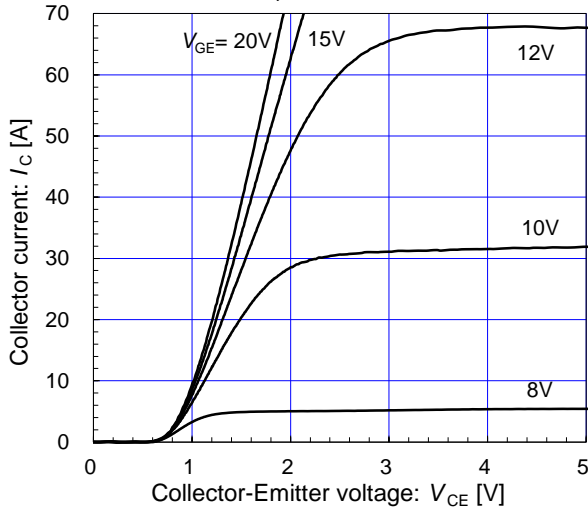


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[Brake]

Collector current vs. Collector-Emittor voltage (typ.)

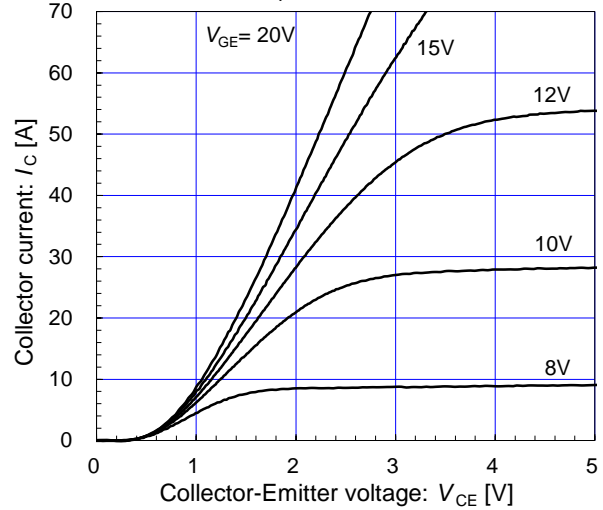
$T_{vj} = 25^\circ\text{C} / \text{chip}$



[Brake]

Collector current vs. Collector-Emittor voltage (typ.)

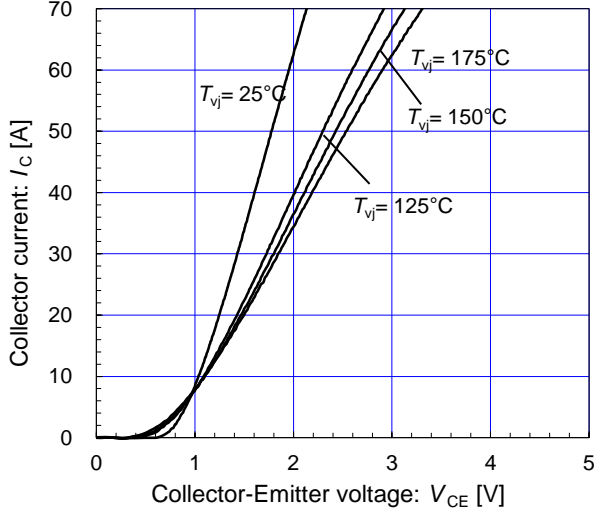
$T_{vj} = 175^\circ\text{C} / \text{chip}$



[Brake]

Collector current vs. Collector-Emittor voltage (typ.)

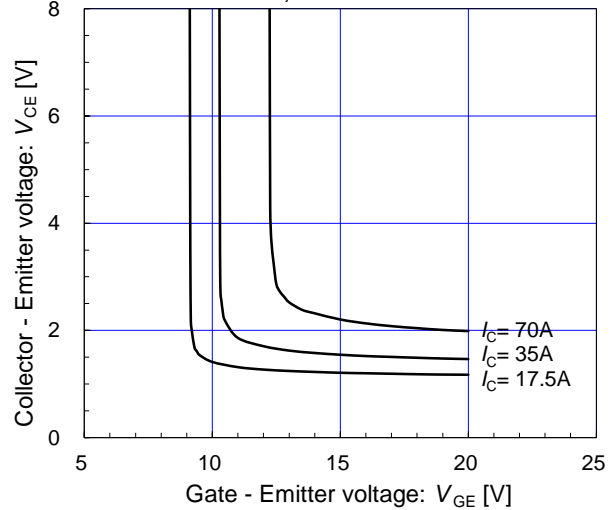
$V_{GE} = 15\text{V} / \text{chip}$



[Brake]

Collector-Emittor voltage vs. Gate-Emittor voltage (typ.)

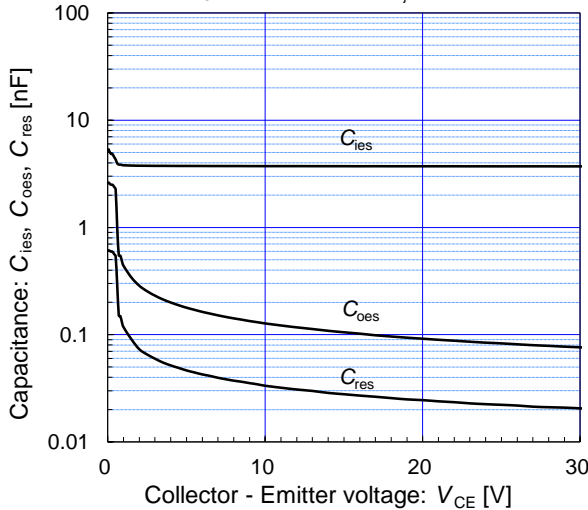
$T_{vj} = 25^\circ\text{C} / \text{chip}$



[Brake]

Capacitance vs. Collector-Emittor voltage (typ.)

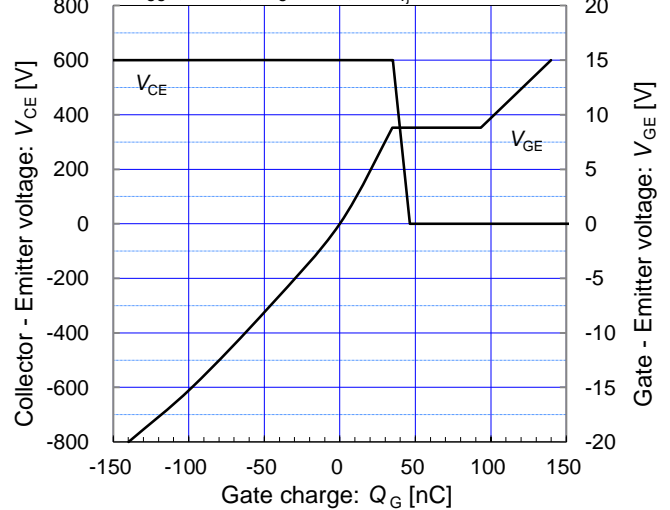
$V_{GE} = 0\text{V}, f = 1\text{MHz}, T_{vj} = 25^\circ\text{C}$



[Brake]

Dynamic Gate charge (typ.)

$V_{CC} = 600\text{V}, I_c = 35\text{A}, T_{vj} = 25^\circ\text{C}$



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